

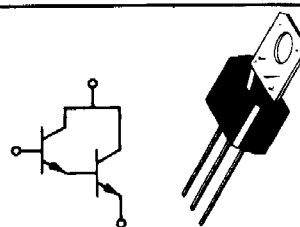
MPS-U45 (SILICON)

NPN SILICON DARLINGTON AMPLIFIER TRANSISTOR

... designed for amplifier and driver applications.

- High DC Current Gain –
 $h_{FE} = 25,000$ (Min) @ $I_C = 200$ mA dc
 $15,000$ (Min) @ $I_C = 500$ mA dc
- Collector-Emitter Breakdown Voltage –
 $BV_{CES} = 40$ Vdc (Min) @ $I_C = 100$ μ A dc
- Low Collector-Emitter Saturation Voltage –
 $V_{CE(sat)} = 1.5$ Vdc @ $I_C = 1.0$ A dc
- Monolithic Construction for High Reliability
- Complement to PNP MPS-U95

NPN SILICON DARLINGTON TRANSISTOR



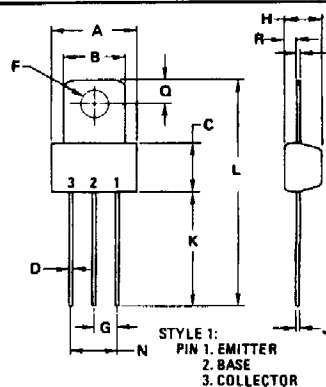
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CES}	40	Vdc
Collector-Base Voltage	V_{CB}	50	Vdc
Emitter-Base Voltage	V_{EB}	12	Vdc
Collector Current	I_C	2.0	A dc
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.0 8.0	Watt mW/ $^\circ\text{C}$
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	10 80	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$ (1)	125	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	12.5	$^\circ\text{C/W}$

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	9.14	9.53	0.360	0.375
B	8.90	7.24	0.260	0.285
C	5.41	5.66	0.213	0.223
D	0.38	0.53	0.015	0.021
F	3.18	3.33	0.126	0.131
G	2.54	BSC	0.100	BSC
H	3.94	4.19	0.155	0.165
J	0.36	0.41	0.014	0.016
K	12.07	12.70	0.475	0.500
L	25.02	25.53	0.985	1.006
N	5.08	BSC	0.200	BSC
Q	2.30	2.68	0.094	0.106
R	1.14	1.40	0.045	0.055



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MPS-U45 (continued)

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 100 \mu\text{A dc}$, $V_{BE} = 0$)	BV_{CES}	40	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100 \mu\text{A dc}$, $I_E = 0$)	BV_{CBO}	50	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \mu\text{A dc}$, $I_C = 0$)	BV_{EBO}	12	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 30 \text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	—	100	nA dc
Emitter Cutoff Current ($V_{EB} = 10 \text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	—	100	nA dc
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 200 \text{ mA dc}$, $V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 500 \text{ mA dc}$, $V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 1.0 \text{ A dc}$, $V_{CE} = 5.0 \text{ Vdc}$)	h_{FE}	25,000 15,000 4,000	65,000 35,000 12,000	150,000 — —	—
Collector-Emitter Saturation Voltage ($I_C = 1.0 \text{ A dc}$, $I_B = 2.0 \text{ mA dc}$)	$V_{CE(sat)}$	—	1.2	1.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 1.0 \text{ A dc}$, $I_B = 2.0 \text{ mA dc}$)	$V_{BE(sat)}$	—	1.85	2.0	Vdc
Base-Emitter On Voltage ($I_C = 1.0 \text{ A dc}$, $V_{CE} = 5.0 \text{ Vdc}$)	$V_{BE(on)}$	—	1.7	2.0	Vdc
DYNAMIC CHARACTERISTICS					
Small-Signal Current Gain (1) ($I_C = 200 \text{ mA dc}$, $V_{CE} = 5.0 \text{ Vdc}$, $f = 100 \text{ MHz}$)	$ h_{fe} $	1.0	3.2	—	—
Collector Base Capacitance ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)	C_{cb}	—	2.5	6.0	pF

(1) Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

Uniwatt darlington transistors can be used in any number of low power applications, such as relay drivers, motor control and as general purpose amplifiers. As an audio amplifier these devices, when used as a complementary pair, can drive 3.5 watts into a 3.2 ohm speaker using a 14 volt supply with less than one per cent distortion. Because of the high gain the base drive requirement is as low as 1 mA in this application. They are also useful as power drivers for high current application such as voltage regulators.